

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

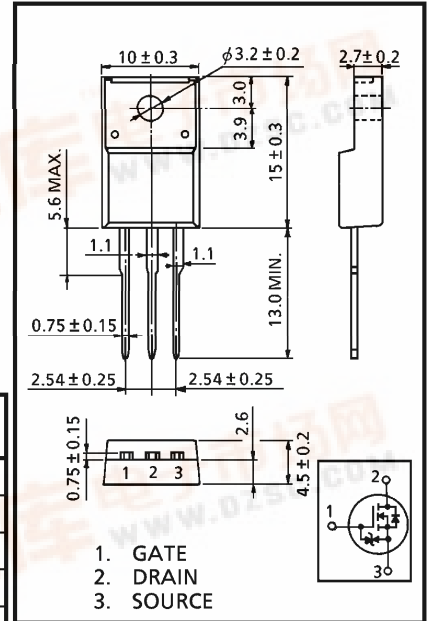
2SK2750

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 1.7 \Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 3.0 S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu A$ (Max.) ($V_{DS} = 600 V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0 V$
($V_{DS} = 10 V, I_D = 1 mA$)



MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	600	V
Drain-Gate Voltage ($R_{GS} = 20 k\Omega$)	V_{DGR}	600	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	I_D	3.5 A
	Pulse	I_{DP}	14 A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	35	W
Single Pulse Avalanche Energy**	E_{AS}	201	mJ
Avalanche Current	I_{AR}	3.5	A
Repetitive Avalanche Energy*	E_{AR}	3.5	mJ
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B

Weight : 1.9 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.57	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90 V, T_{ch} = 25^\circ C$ (initial), $L = 28.8 mH, R_G = 25 \Omega, I_{AR} = 3.5 A$

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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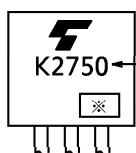
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA	
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	—	—	V	
Gate Threshold Voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 1.8 \text{ A}$	—	1.7	2.2	Ω	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 1.8 \text{ A}$	2.0	3.0	—	S	
Input Capacitance	C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	—	800	—	pF	
Reverse Transfer Capacitance	C_{rss}		—	6	—		
Output Capacitance	C_{oss}		—	65	—		
Switching Time	Rise Time	t_r		—	15	—	ns
	Turn-on Time	t_{on}		—	50	—	
	Fall Time	t_f		—	15	—	
	Turn-off Time	t_{off}		—	85	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} \cong 400 \text{ V}, V_{GS} = 10 \text{ V},$ $I_D = 3.5 \text{ A}$	—	20	—	nC	
Gate-Source Charge	Q_{gs}		—	10	—		
Gate-Drain ("Miller") Charge	Q_{gd}		—	10	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	3.5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	14	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	1400	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	9	—	μC

MARKING

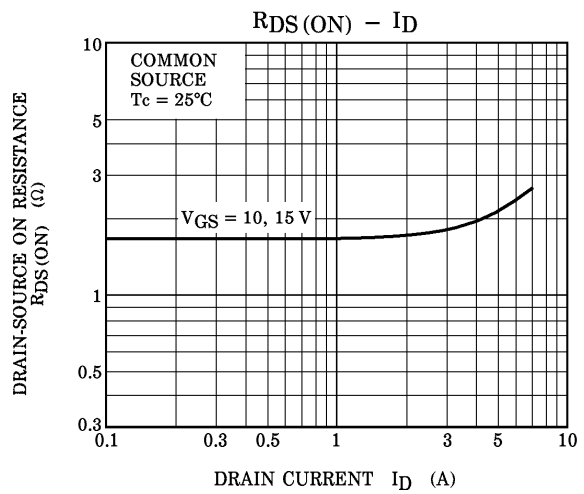
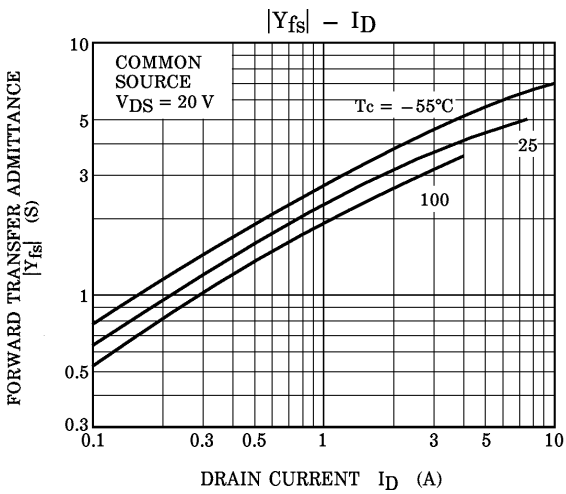
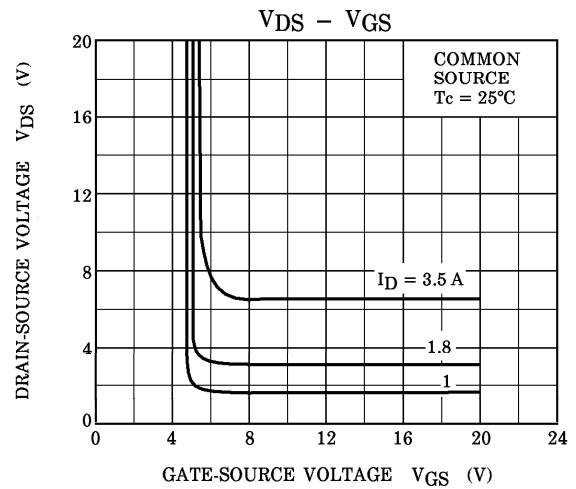
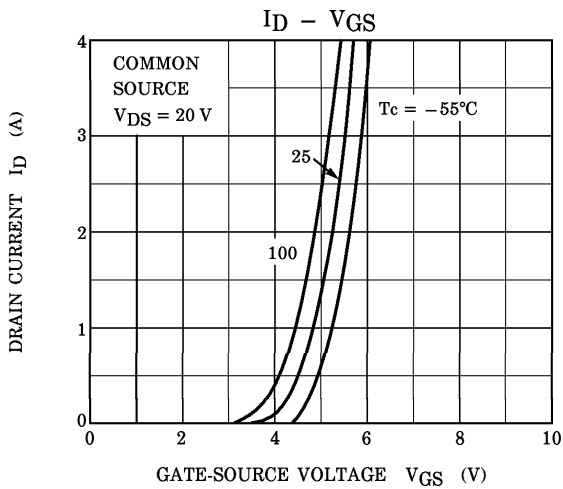
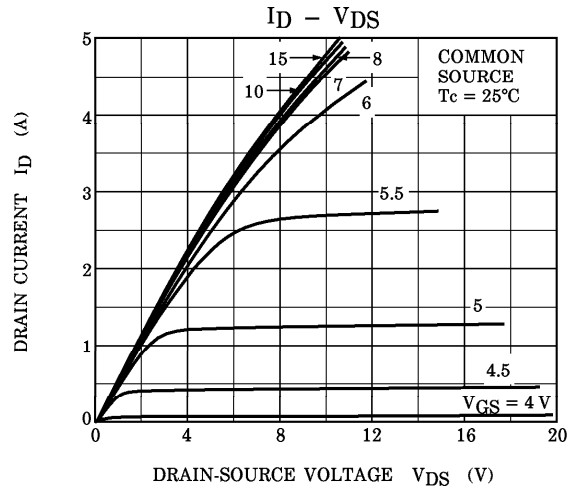
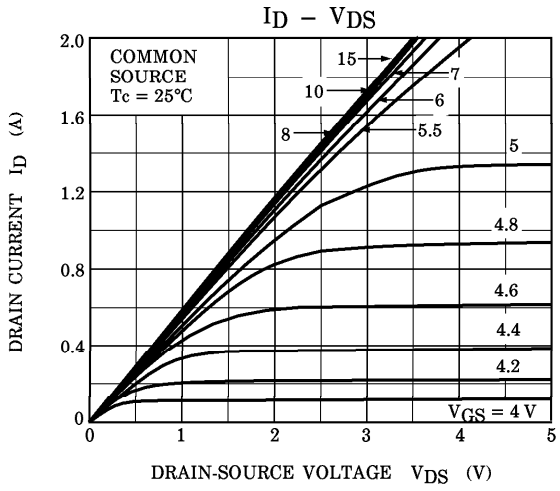


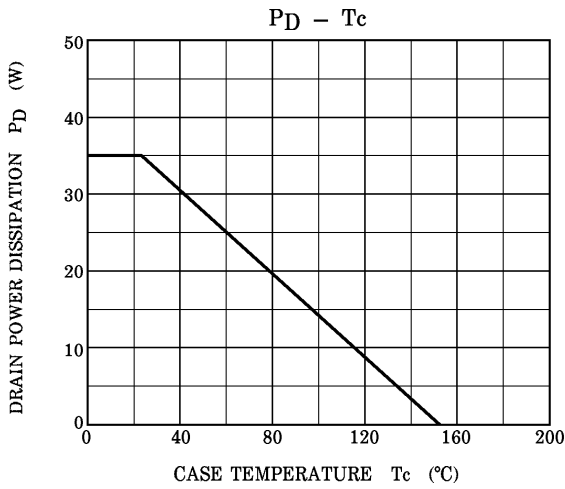
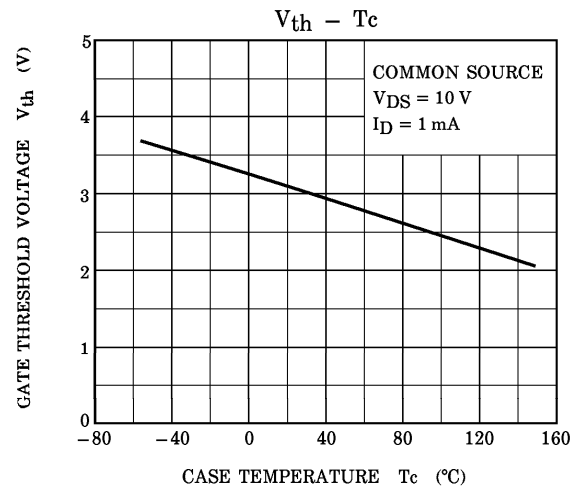
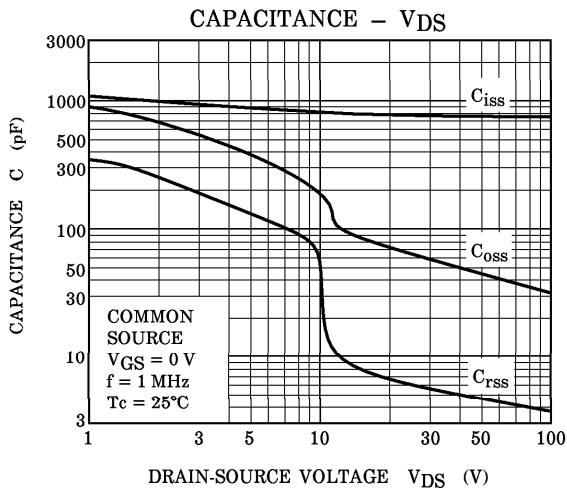
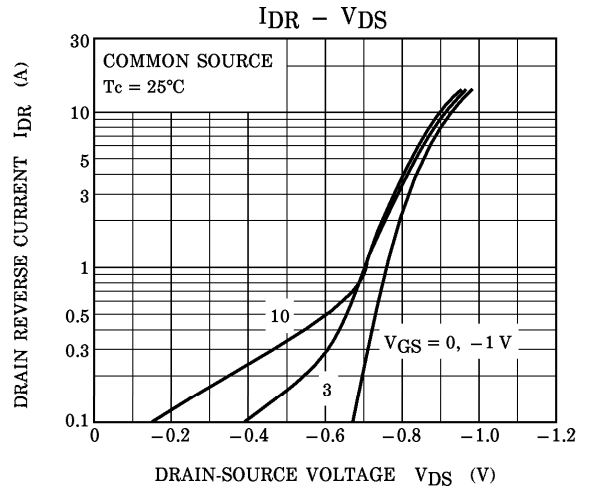
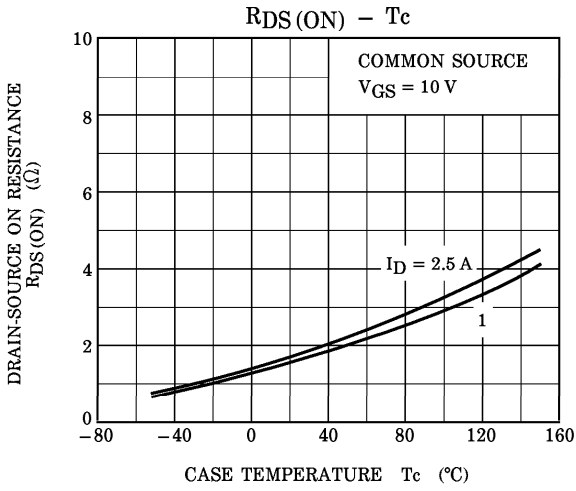
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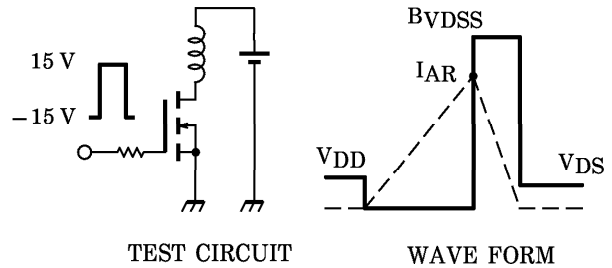
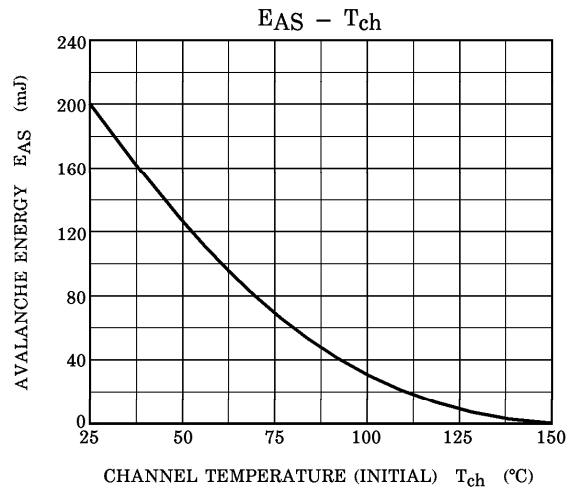
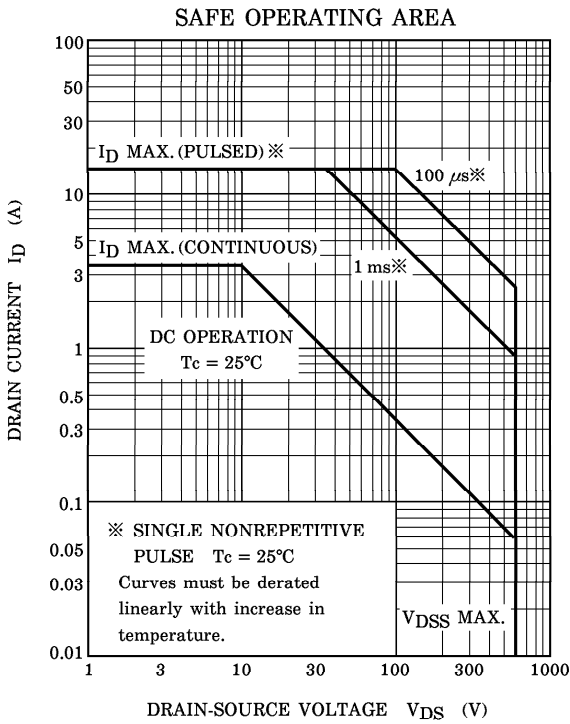
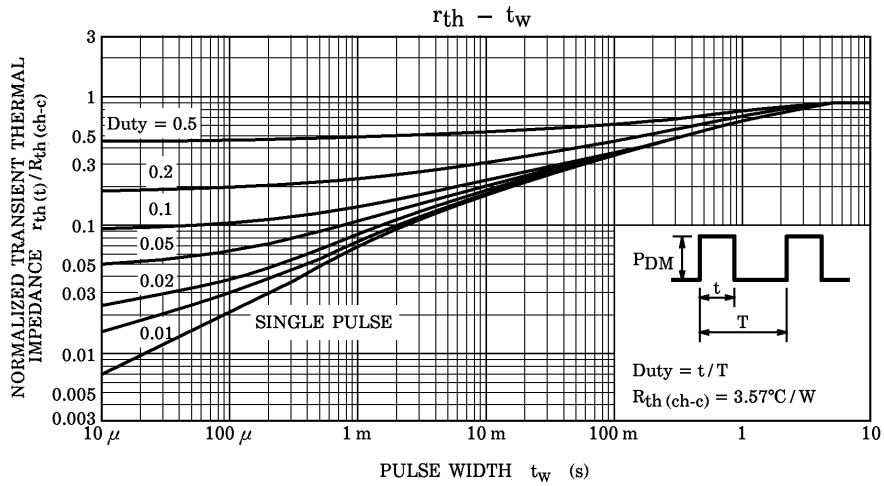
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 3.5 \text{ A}$, $R_G = 25 \Omega$ $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$
 $V_{DD} = 90 \text{ V}$, $L = 28.8 \text{ mH}$